

**Silicon NPN Power Transistor**

**KSD5072**

**DESCRIPTION**

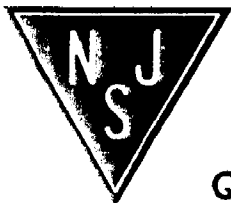
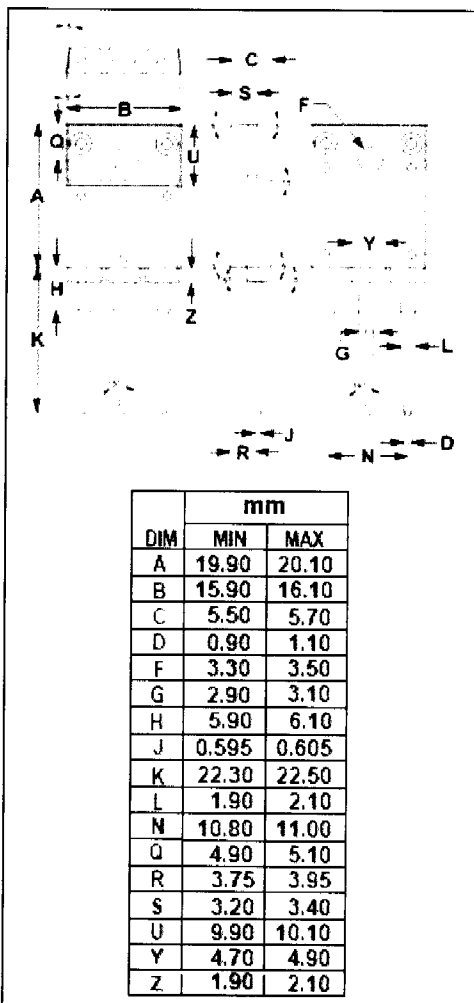
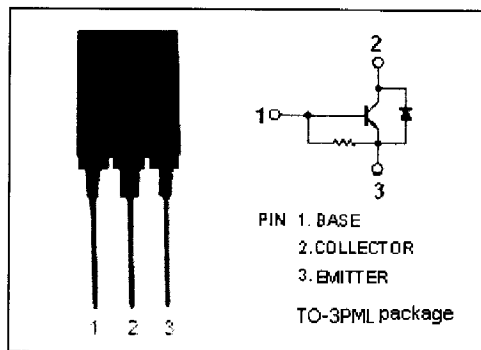
- High Breakdown Voltage-  
 :  $V_{CBO} = 1500V$  (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

**APPLICATIONS**

- Designed for color TV horizontal output applications

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	5	A
$I_{CP}$	Collector Current-Peak	16	A
$P_C$	Collector Power Dissipation @ $T_c = 25^\circ C$	60	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



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### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 4A; I_B= 0.8A$			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 4A; I_B= 0.8A$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}= 800V; I_E= 0$			10	$\mu A$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}= 4V; I_C= 0$	40		200	mA
$h_{FE}$	DC Current Gain	$I_C= 1A; V_{CE}= 5V$	8			
$f_T$	Current-Gain—Bandwidth Product	$I_C= 1A; V_{CE}= 10V$		3		MHz
$V_{ECF}$	C-E Diode Forward Voltage	$I_F= 5A$			2.0	V
$t_f$	Fall Time	$I_C= 4A, I_{B1}= 0.8A; I_{B2}= -1.6A$ $R_L= 50\ \Omega; V_{CC}= 200V$			0.4	$\mu s$